

INFORMATION DISCLOSURE CITATION PTO-1449			Atty. Docket No. NTI-023-1D		Serial No. Filed Herewith	
			Applicant LIU, Yong		Group Filed Herewith	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>AL</i>	4,231,811	11/4/1980	Somekh, et al.	148	1.5	9/13/1979
	4,426,584	1/17/1984	Bohlen, et al.	250	492.2	6/3/1981
	4,456,371	6/26/1984	Lin	355	71	6/30/1982
	4,812,962	3/14/1989	Witt	364	490	4/9/1987
	4,895,780	1/23/1990	Nissan-Cohen, et al.	430	5	10/25/1988
	4,902,899	2/20/1990	Lin, et al.	250	492.1	6/1/1987
	5,051,598	9/24/1991	Ashton, et al.	250	492.2	9/12/1990
	5,182,718	1/26/1993	Harafuji, et al.	364	490	3/29/1990
	5,208,124	5/4/1993	Sporon-Fiedler, et al.	430	5	3/19/1991
	5,241,185	8/31/1993	Meiri, et al.	250	492.2	1/8/1992
	5,242,770	9/7/1993	Chen, et al.	430	5	1/16/1992
	5,256,505	10/26/1993	Chen, et al.	430	5	8/21/1992
	5,326,659	7/5/1994	Liu, et al.	430	5	3/5/1992
	5,340,700	8/23/1994	Chen, et al.	430	312	11/3/1993
	5,432,714	7/11/1995	Chung, et al.	364	525	9/2/1994
	5,447,810	9/5/1995	Chen, et al.	430	5	2/9/1994
	5,498,579	3/12/1996	Borodovsky, et al.	437	250	6/8/1994
	5,553,273	9/3/1996	Liebmann	395	500	4/17/1995
	5,553,274	9/3/1996	Liebmann	395	500	6/6/1995
	5,572,598	11/5/1996	Wihl, et al.	382	144	2/25/1994
	5,631,110	5/20/1997	Shioiri, et al.	430	5	6/5/1995
	5,636,002	6/3/1997	Garofalo	355	53	10/31/1995
<i>AL</i>	5,657,235	8/12/1997	Liebmann, et al.	364	474.24	5/3/1995

EXAMINER:

A. Porosco

Date Considered:

3/25/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-023-1D		Serial No. Filed Herewith		
		Applicant LIU, Yong				
		Filing Date Filed Herewith		Group		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>DL</i>	5,663,017	9/2/1997	Schinella, et al.	430	5	6/7/1995
	5,663,893	9/2/1997	Wampler, et al.	364	491	5/3/1995
	5,682,323	10/28/1997	Paschi, et al.	364	491	3/6/1995
	5,705,301	1/6/1998	Garza, et al.	430	5	2/27/1996
	5,707,765	1/13/1998	Chen	430	5	5/28/1996
	5,723,233	3/3/1998	Garza, et al.	430	5	2/27/1996
	5,740,068	4/14/1998	Liebmann, et al.	364	489	5/30/1996
	5,766,806	6/16/1998	Spence	430	5	9/9/1996
	5,795,688	8/18/1998	Burdorf, et al.	430	30	8/14/1996
	5,801,954	9/1/1998	Le, et al.	364	488	4/24/1996
	5,804,340	9/8/1998	Garza, et al.	430	5	12/23/1996
	5,815,685	9/29/1998	Kamon	395	500	9/15/1995
	5,821,014	10/13/1998	Chen, et al.	430	5	2/28/1997
	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
	5,827,623	10/27/1998	Ishida, et al.	430	5	10/30/1996
	5,847,959	12/8/1998	Veneklasen, et al.	364	468.28	1/28/1997
	5,862,058	1/19/1999	Samuels, et al.	364	491	5/16/1996
	5,863,682	1/26/1999	Abe, et al.	430	30	2/21/1997
	5,879,844	3/9/1999	Yamamoto, et al.	430	30	12/20/1996
	5,885,734	3/23/1999	Pierrat, et al.	430	5	8/15/1996
	5,900,338	5/4/1999	Garza, et al.	430	5	8/15/1997
	5,958,635	9/28/1999	Reich, et al.	430	30	10/20/1997
<i>DL</i>	5,972,541	10/26/1999	Sugasawara, et al.	430	5	3/4/1998

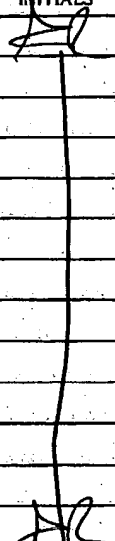
EXAMINER:

A. D. Brown

Date Considered:

3/25/04

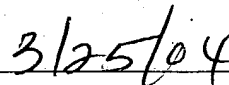
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-023-1D		Serial No. Filed Herewith		
		Applicant LIU, Yong				
		Filing Date Filed Herewith		Group		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	5,994,002	11/30/1999	Matsuoka	430	5	9/4/1997
	6,007,310	12/28/1999	Jacobsen, et al.	417	362	5/23/1997
	6,009,250	12/28/1999	Ho, et al.	395	500.06	9/30/1997
	6,009,251	12/28/1999	Ho, et al.	395	500.06	9/30/1997
	6,011,911	1/4/2000	Ho, et al.	395	500.06	9/30/1997
	6,077,310	6/20/2000	Yamamoto, et al.	716	19	1/29/1999
	6,078,738	6/20/2000	Garza, et al.	395	500.22	5/8/1997
	6,081,658	6/27/2000	Rieger, et al.	395	500.22	12/31/1997
	6,081,659	6/27/2000	Garza, et al.	395	500.22	4/26/1999
	6,114,071	9/5/2000	Chen, et al.	430	5	4/6/1998
	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
	6,171,731 B1	1/9/2001	Medvedeva, et al.	430	5	1/20/1999
	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

EXAMINER:



Date Considered:



EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449			Atty. Docket No. NTI-023-1D		Serial No. Filed Herewith	
			Applicant LIU, Yong		Group	
			Filing Date Filed Herewith			
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
EC	5,282,140	1/25/1994	Tazawa, et al.	364	468	6/24/1992
	6,014,456	1/11/2000	Tsudaka	382	144	7/15/1996
	6,154,563	11/28/2000	Tsudaka	382	144	12/17/1998
	6,225,025 B1	5/1/2001	Hoshino	430	296	9/22/1998
	6,298,473 B1	10/2/2001	Ono, et al.	716	21	12/3/1998
	6,339,836 B1	1/15/2002	Eisenhofer, et al.	716	5	8/24/1998
	6,453,457 B1	9/17/2002	Pierrat, et al.	716	19	9/29/2000
	2002/0076622 A1	6/20/2002	Pierrat, et al.	430	5	12/20/2000
	2002/0100004 A1	7/25/2002	Pierrat, et al.	716	5	3/15/2002
	AB2					

EXAMINER:

A. Drasco

Date Considered:

3/25/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No.	Serial No.
	NTI-023-1D	Filed Herewith
	Applicant	
	LIU, Yong	
	Filing Date	Group
	Filed Herewith	

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>JS</i>	5,991,006	11/23/0199	Tsudaka	355	53	10/27/1997
	6,016,357	1/18/2000	Neary, et al.	382	144	6/16/1997
	6,091,845	7/18/2000	Pierrat, et al.	382	144	2/24/1998
	6,272,236	8/7/2001	Pierrat, et al.	382	144	7/18/2000
	6,243,855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998
	2002/0019729 A1	2/14/2002	Chang, et al.	703	6	8/7/1998
<i>JS</i>	2002/0035461 A1	3/21/2002	Chang, et al.	703	13	7/16/2001
<i>JS</i>	6,183,916	2/06/2001	Kuo et al.	430	5	9/13/1999
<i>JS</i>	6,425,117	7/23/2002	Pasch et al.	716	21	9/29/1997

EXAMINER:

J. Proasce

Date Considered:

3/25/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-023-1D		Serial No. Filed Herewith			
		Applicant LIU, Yong		Group			
		Filing Date Filed Herewith					
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
AP	WO 00/36525 A2	6/22/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	3-80525	4/5/1991	JP			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67074 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67075 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67076 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>
	3-210560	9/13/1991	JP			<input type="checkbox"/>	<input type="checkbox"/>
	8-236317	9/6/1996	JP			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/47981	9/23/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
	10-133356	5/22/1998	JP			<input type="checkbox"/>	<input type="checkbox"/>
AP	11-143085	5/28/1999	JP			<input type="checkbox"/>	<input type="checkbox"/>

EXAMINER:

A. Rosasco

Date Considered:

3/25/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-023-1D		Serial No. Filed Herewith			
		Applicant LIU, Yong		Group Filed Herewith			
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<i>[Signature]</i>	WO 99/14706 A2/A3	3/25/1999	WO	—	—	<input type="checkbox"/>	<input type="checkbox"/>


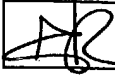
EXAMINER:

A. Ponsio

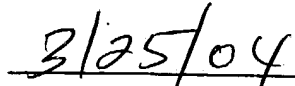
Date Considered:

3/25/04



EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-023-1D	Serial No. Filed Herewith
		Applicant LIU, Yong	Group Filed Herewith
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	Ackmann, P., et al., "Phase Shifting and Optical Proximity Corrections to Improve CD Control on Logic Devices in Manufacturing for Sub 0.35 um I-Line", Advance Micro Devices (8 pages).		
	Chen, J.F., et al., "Optical Proximity Correction for Intermediate-Pitch Features Using Sub-Resolution Scattering Bars", MicroUnity Systems Engineering, Inc., Sunnyvale, California, pp. 1-16.		
	Chen, J.F., et al., "Practical Method for Full-Chip Optical Proximity Correction", MicroUnity Systems Engineering, Inc., Sunnyvale, California (14 pages).		
	Cobb, et al., "Fast Sparse Aerial Image Calculation for OPC", SPIE, Vol. 2621, pp. 534-544.		
	Lithas, "Lithas: Optical Proximity Correction Software" (2 pages).		
	Microunity, "OPC Technology & Product Description", MicroUnity Systems Engineering, Inc., pp. 1-5.		
	Precim, "Proxima System", Precim Company, Portland, Oregon (2 pages).		
	Precim, "Proxima Wafer Proximity Correction System", Precim Company, Portland, Oregon (2 pages).		
	Rieger, M., et al., "Mask Fabrication Rules for Proximity-Corrected Patterns", Precim Company, Portland, Oregon (10 pages).		
	Rieger, M., et al., "Using Behavior Modeling for Proximity Correction", Precim Company, Portland, Oregon (6 pages).		
	Stimman, J., et al., "Spatial Filter Models to Describe IC Lithographic Behavior", Precim Corporation, Portland, Oregon (10 pages).		
	Choi, Y., et al., "Optical Proximity Correction on Attenuated Phase Shifting Photo Mask for Dense Contact Array", LG Semicon Company (11 pages).		
	Lucas, K., et al., "Model Based OPC for 1st Generation 193nm Lithography", Motorola Inc., IDT assignee to IMEC (12 pages).		
	Stimman, J., et al., "Quantifying Proximity and Related Effects in Advanced Wafer Processes", Precim Company, Hewlett Packard Labs (9 pages).		

 EXAMINER:  Date Considered:


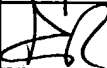


 EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No.	Serial No.
		NTI-023-1D	Filed Herewith
		Applicant	
		LIU, Yong	
		Filing Date	Group
		Filed Herewith	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	Sugawara, M., et al., "Practical Evaluation of Optical Proximity Effect Correction by EDM Methodology", Sony Corporation (11 pages).		
	Granik, Y., et al., "MEEF as a Matrix", Mentor Graphics Corporation (11 pages).		
	Kang, D., et al., "Effects of Mask Bias on the Mask Error Enhancement Factor (MEEF) of Contact Holes" (11 pages).		
	Matsuura, S., et al., "Reduction of Mask Error Enhancement Factor (MEEF) by the Optimum Exposure Dose Self-Adjusted Mask", NEC Corporation (12 pages).		
	Adam, K., et al., "Simplified Models for Edge Transitions in Rigorous Mask Modeling", University of California Berkeley (40 pages).		
	Gordon, R., et al., "Mask Topography Simulation for EUV Lithography", FINLE Technologies Inc. (15 pages).		
	Pistor, T., "Rigorous 3D Simulation of Phase Defects in Alternating Phase-Shifting Masks", Panoramic Technology Inc. (13 pages).		
	Semmner, A., et al., "Application of 3D EMF Simulation for Development and Optimization of Alternating Phase Shifting Masks", Infineon Technologies AG (12 pages).		
	Wong, A., et al., "Polarization Effects in Mask Transmission", University of California Berkeley (8 pages).		
	Neureuther, A., et al., "Modeling Defect-Feature Interactions in the Presence of Aberrations", University of California Berkeley (10 pages).		
	Trans Vector, "Now Better Quality Photomasks", Trans Vector Technologies, Inc., Camarillo, California (4 pages).		
	Saleh, B., et al., "Reduction of Errors of Microphotographic Reproductions by Optimal Corrections of Original Masks", Optical Engineering, Vol. 20, No. 5, pp. 781-784, September/October 1981.		
	Mathur, B.P., et al., "Quantitative Evaluation of Shape of Image on Photoresist of Square Apertures", IEEE, Transactions On Electron Devices, Vol. 35, No. 3, pp. 294-297, March 1988.		
	Lin, B.J., "Methods to Print Optical Images at Low-k1 Factors", SPIE, Optical/Laser Microlithography III, Vol. 1264, pp. 2-13 (1990).		

EXAMINER: Date Considered: 3/25/04

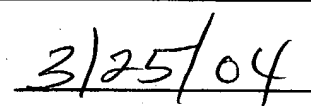
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-023-1D	Serial No. Filed Herewith
		Applicant LIU, Yong	
		Filing Date Filed Herewith	Group
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	Henke, W., et al., "A Study of Reticule Defects Imaged Into Three-Dimensional Developed Profiles of Positive Photoresist Using the Solid Lithography Simulator", Microelectronics Eng., Vol. 14, pp. 283-297 (1991)		
	Wiley, J., et al., "Phase Shift Mask Pattern Accuracy Requirements and Inspection Technology", SPIE, Integrated Circuit Metrology, Inspection, And Process Control V, Vol. 1464, pp. 346-355 (1991).		
	Fu, C.C., et al., "Enhancement of Lithographic Patterns by Using Serif Features", IEEE, Transactions On Electron Devices, Vol. 38, No. 12, pp. 2599-2603, December 1991.		
	Ohtsuka, H., et al., "Phase Defect Repair Method for Alternating Phase Shift Masks Conjugate Twin-Shifter Method", Jpn. J. Appl. Phys., Vol. 31, pp. 4143-4149 (1992).		
	Crisalle, O., et al., "A Comparison of the Optical Projection Lithography Simulators in SAMPLE and PROLITH", IEEE, Transactions On Semiconductor Manufacturing, Vol. 5, No. 1, pp. 14-26, February 1992.		
	Garofalo, J., et al., "Mask Assisted Off-Axis Illumination Technique for Random Logic", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2651-2658, November/December 1993.		
	Harafuji, K., et al., "A Novel Hierarchical Approach for Proximity Effect Correction in Electron Beam Lithography", IEEE, Vol. 12, No. 10, pp. 1508-1514, October 1993.		
	Nistler, J., et al., "Phase Shift Mask Defect Printability Analysis", Proceedings Of The Microlithography Seminar INTERFACE '93, OCG Microelectronic Materials, Inc., pp. 11-28 (1993)		
	Rieger, M., et al., "System for Lithography Proximity Compensation", Precim Company, Portland, Oregon, September 1993 (28 pages).		
	Garofalo, J., et al., "Automatic Proximity Correction for 0.35um I-Line Photolithography", IEEE, pp. 92-94 (1994).		
	Pati, Y.C., et al., "Phase-Shifting Masks for Microlithography: Automated Design and Mask Requirements", J. Opt. Soc. Am., Vol. 11, No. 9, pp. 2438-2452, September 1994.		
	Pierrat, C., et al., "A Rule-Based Approach to E-Beam and Process-Induced Proximity Effect Correction for Phase-Shifting Mask Fabrication", SPIE, Vol. 2194, pp. 298-309 (1994).		
	Spence, C., et al., "Automated Determination of CAD Layout Failures Through Focus: Experiment and Simulation", SPIE, Vol. 2197, pp. 302-313 (1994).		
	Stirnuman, J., et al., "Fast Proximity Correction with Zone Sampling", SPIE, Vol. 2197, pp. 294-301 (1994).		


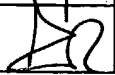
EXAMINER:



Date Considered:



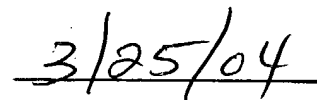
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No.	Serial No.
		NTI-023-1D	Filed Herewith
		Applicant	
		LIU, Yong	
		Filing Date	Group
		Filed Herewith	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	Sturman, J., et al., "Optimizing Proximity Correction for Wafer Fabrication Processes", SPIE, Photomask Technology And Management, Vol. 2322, pp. 239-246 (1994).		
	Sturman, J., et al., "Wafer Proximity Correction and Its Impact on Mask-Making", Bacus News, Vol. 10, Issue 1, pp. 1, 3-7, 10-12, January 1994.		
	Qian, Q.D., et al., "A New Scalar Planewave Model for High NA Lithography Simulations", IEEE, pp. 45-48 (1994).		
	Henderson, R., et al., "Optical Proximity Effect Correction: An Emerging Technology", Microlithography World, pp. 6-12 (1994).		
	Barouch, E., et al., "OPTIMASK: An OPC Algorithm for Chrome and Phase-Shift Mask Design", SPIE, Vol. 2440, pp. 192-206, February 1995.		
	Garofalo, J., et al., "Automated Layout of Mask Assist-Features for Realizing 0.5k1 ASIC Lithography", SPIE, Vol. 2440, pp. 302-312 (1995).		
	Karklin, L., "A Comprehensive Simulation Study of the Photomask Defects Printability", SPIE, Vol. 2621, pp. 490-504 (1995).		
	Wiley, J., et al., "The Effect of Off-Axis Illumination on the Printability of Opaque and Transparent Reticle Defects", SPIE, Vol. 2512, pp. 432-440 (1995).		
	Brunner, T., et al., "Approximate Models for Resist Processing Effects", SPIE, Vol. 2726, pp. 198-207, March 1996.		
	Rieger, M., et al., "Customizing Proximity Correction for Process-Specific Objectives", SPIE, Vol. 2726, pp. 651-659 (1996).		
	Yen, A., et al., "Characterization and Correction of Optical Proximity Effects in Deep-Ultraviolet Lithography Using Behavior Modeling", J. Vac. Sci. Technol. B, Vol. 14, No. 6, pp. 4175-4178, November/December 1996.		
	Chang, K., et al., "Accurate Modeling of Deep Submicron Interconnect Technology", TMA Times, Vol. IX, No. 3 (1997).		
	Chen, J.F., et al., "Full-Chip Optical Proximity Correction with Depth of Focus Enhancement", Microlithography World (1997).		
	Gans, F., et al., "Printability and Repair Techniques for DUV Photomasks", SPIE, Proceedings Of The 17th Annual Symposium On Photomask Technology And Management, Vol. 3236, pp. 136-141 (1997).		

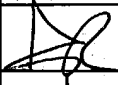

EXAMINER:



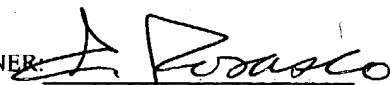
Date Considered:



EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No.	Serial No.
		NTI-023-1D	Filed Herewith
		Applicant	
		LIU, Yong	
		Filing Date	Group
		Filed Herewith	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	Ibsen, K., et al., "Clear Field Reticle Defect Disposition for Advanced Sub-Half Micron Lithography", SPIE, Proceedings Of The 17th Annual Symposium On Photomask Technology And Management, Vol. 3236, pp. 124-135 (1997).		
	Morimoto, H., et al., "Next Generation Mask Strategy - Technologies are Ready for Mass Production of 256MDRAM?", SPIE, Vol. 3236, pp. 188-189 (1997).		
	Park, C., et al., "An Automatic Gate CD Control for a Full Chip Scale SRAM Device", SPIE, Vol. 3236, pp. 350-357 (1997).		
	Pati, Y.C., et al., "Exploiting Structure in Fast Aerial Image Computation for Integrated Circuit Patterns", IEEE Transactions On Semiconductor Manufacturing, Vol. 10, No. 1, pp. 62-74, February 1997.		
	Vacca, A., et al., "100nm Defect Detection Using a Dynamically Programmable Image Processing Algorithm", SPIE, Vol. 3236 (1997) (Abstract Only).		
	Dolainsky, C., et al., "Application of a Simple Resist Model to Fast Optical Proximity Correction", SPIE, Vol. 3051, pp. 774-780 (1997).		
	Chen, J., et al., "Full-Chip Optical Proximity Correction with Depth of Focus Enhancement", Microlithography World, (5 pages) (1997).		
	Asai, N., et al., "Proposal for the Coma Aberration Dependent Overlay Error Compensation Technology", Jpn. J. Appl. Phys., Vol. 37, pp. 6718-6722 (1998).		
	Gotoh, Y., et al., "Pattern Dependent Alignment Technique for Mix-and-Match Electron-Beam Lithography with Optical Lithography", J. Vac. Sci. Technol. B, Vol. 16, No. 6, pp. 3202-3205, November/December 1998.		
	Kubota, H., et al., "A Fast Method of Simulating Resist Pattern Contours Based on Mean Inhibitor Concentration", Jpn. J. Appl. Phys., Vol. 37, pp. 5815-5820 (1998).		
	Vacca, A., et al., "100nm Defect Detection Using an Existing Image Acquisition System", SPIE, Vol. 3236, pp. 208-21 (1998).		
	Wong, A., et al., "Lithographic Effects of Mask Critical Dimension Error", SPIE, Vol. 3334, pp. 106-115 (1998).		
	Fukuda, H., et al., "Determination of High-Order Lens Aberration Using Phase/Amplitude Linear Algebra", J. Vac. Sci. Technol. B, Vol. 17, No. 6, pp. 3318-3321, November/December 1999.		
	Fukuda, H., "Node-Connection/Quantum Phase-Shifting Mask: Path to Below 0.3um Pitch, Proximity Effect Free, Random Interconnects and Memory Patterning", J. Vac. Sci. Technol. B, Vol. 17, No. 6, pp. 3291-3295, November/December 1999.		

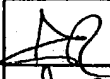
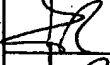


EXAMINER:



Date Considered:

3/25/04

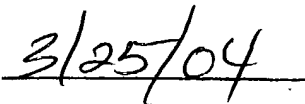
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-023-1D	Serial No. Filed Herewith
		Applicant LIU, Yong	Group Filed Herewith
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	Spence, C., et al., "Integration of Optical Proximity Correction Strategies in Strong Phase Shifters Design for Poly-Gate Layers", Bacus News, Vol. 15, Issue 12, pp. 1, 4-13, December 1999.		
	Balasinski, A., et al., "A Novel Approach to Simulate the Effect of Optical Proximity on MOSFET Parametric Yield", IEEE, pp. 37.6.1-37.6.4 (1999).		
	Balasinski, A., et al., "Comparison of Mask Writing Tools and Mask Simulations for 0.16um Devices", IEEE, SEMI Advanced Semiconductor Manufacturing Conference, pp. 372-377 (1999).		
	Wong, A., et al., "Asymmetric Biasing for Subgrid Pattern Adjustment", SPIE, Vol. 4346, pp. 1-6 (2001).		

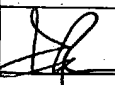
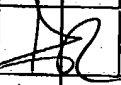
EXAMINER:



Date Considered:



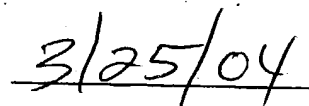
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No.	Serial No.
		NTI-023-1D	Filed Herewith
		Applicant	
		LIU, Yong	
		Filing Date	Group
		Filed Herewith	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
	Cobb, N., et al., "Fast, Low-Complexity Mask Design", SPIE, Vol. 2440, pp. 313-327, February 22-24, 1995.		
	Cobb, N., et al., "Experimental Results on Optical Proximity Correction With Variable Threshold Resist Model", SPIE, Vol. 3051, pp. 458-468, March 12-14, 1997.		
	Cobb, N., "Fast Optical and Process Proximity Correction Algorithms for Integrated Circuit Manufacturing", Dissertation, University of California at Berkeley, UMI Microform 9902038 (139 pages).		
	Uhring, W., et al., "Model of an Instrumented Opto-Electronic Transmission System in HDL-A and VHDL-AMS", SPIE, Vol. 3893, pp. 137-146, October 1999.		
	Cooke, M., "OPC/PSM Designs For Poly Gate Layers", European Semiconductor, Vol. 22, No. 7, pp. 57-59, July 2000.		
	Granik, Y., et al., "Sub-Resolution Process Windows And Yield Estimation Technique Based On Detailed Full-Chip CD Simulation", SPIE, Vol. 4182, pp. 335-341 (2000).		
	Schellenberg, F., et al., "OPC Beyond 0.18um: OPC on PSM Gates", SPIE, Vol. 4000, pp. 1062-1069, March 1-3, 2000.		
	Toublan, O., et al., "Phase Aware Proximity Correction for Advanced Masks", SPIE, Vol. 4000, pp. 160-170, March 1-3, 2000.		


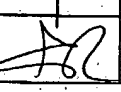
EXAMINER:



Date Considered:



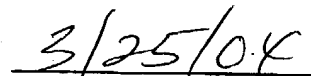
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. NTI-023-1D Applicant LIU, Yong Filing Date Filed Herewith	Serial No. Filed Herewith Group
	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
EXAMINER'S INITIALS	CITATION	
	Erdmann, A., "Topography Effects and Wave Aberrations in Advanced PSM-Technology", Fraunhofer Institute of Integrated Circuits (11 pages).	
	Toublan, O., et al., "Phase and Transmission Errors Aware OPC Solution for PSM: Feasibility Demonstration", Mentor Graphics Corp. (7 pages).	
	Neureuther, A., "Modeling Phase Shifting Masks", SPIE, 10th Annual Symposium On Microlithography, Vol. 1496, pp. 80-85 (1990).	
	Brunner, T., "Impact of Lens Aberrations on Optical Lithography", IBM J. Res. Develop., Vol. 41, No. 1/2, pp. 57-67, January/March 1997.	
	Tsujimoto, E., et al., "Hierarchical Mask Data Design System (PROPHET) for Aerial Image Simulation, Automatic Phase-Shifter Placement, and Subpeak Overlap Checking", SPIE, Vol. 3096, pp. 163-172 (1997).	
	Schoenmaker, W., et al., "Theory and Implementation of a New Interpolation Method Based on Random Sampling", IMEC Technology Paper, pp. 1-35, 31 January 1997.	
	Chuang, H., et al., "Practical Applications of 2-D Optical Proximity Corrections for Enhanced Performance of 0.25um Random Logic Devices", IEEE, pp. 18.7.1-18.7.4, December 1997.	

EXAMINER:



Date Considered:



EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.